

General Description

The DMG6968UTS is the highest performance trench

N-ch MOSFETs with extreme high cell density,

which provide excellent RDSON and gate charge

for most of the small power switching and

load switch applications. The meet the RoHS and

Product requirement with full function reliability approved.

General Features

V_{DS} = 20V I_D = 7A

 $R_{DS(ON)}$ < 14m Ω @ V_{GS}=4. 5V

 $R_{DS(ON)} < 17m\Omega @ V_{GS}=2.5V$

Application

Battery protection

Load switch

Uninterruptible power supply

Package Marking and Ordering Information

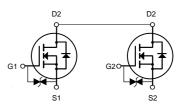
Product ID	Pack	Brand	Qty(PCS)
DMG6968UTS	TSSOP-8	HXY MOSFET	5000

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

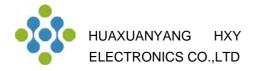
Symbol	Parameter	Limit	Unit
Vds	Drain-Source Voltage	20	V
Vgs	Gate-Source Voltage	±10	V
I _D	Drain Current-Continuous	7	A
Ідм	Drain Current-Pulsed (Note 1)	23	A
PD	Maximum Power Dissipation	1.25	W
Tj,Tstg	Operating Junction and Storage Temperature Range	-55 To 150	°C
Reja	Thermal Resistance, Junction-to-Ambient (Note 2)	111	°C /W



TSSOP-8



Dual N-Channel MOSFET



Electrical Characteristics (T_A=25[°]Cunless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Мах	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V_{GS} =0V I _D =250µA	A 20		-	V
Zero Gate Voltage Drain Current	ldss	V _{DS} =16V,V _{GS} =0V			1	μA
Gate-Body Leakage Current	lgss	$V_{GS}=\pm 8V, V_{DS}=0V$			±100	nA
Gate Threshold Voltage	VGS(th)	$V_{DS}=V_{GS}$, $I_D=250\mu A$	0.5	0.7	1.2	V
		V _{GS} =4.5V, I _D =4.5A	-	12	14	mΩ
Drain-Source On-State Resistance	Rds(on)	V _{GS} =2.5V, I _D =3.5A	-	15	17	mΩ
Forward Transconductance	g⊧s	V _{DS} =5V,I _D =3.5A	-	20	-	S
Input Capacitance	C _{lss}		-	955	-	PF
Output Capacitance	Coss	V _{DS} =8V,V _{GS} =0V,	-	200	-	PF
Reverse Transfer Capacitance	Crss	F=1.0MHz	-	150	-	PF
Turn-on Delay Time	td(on)		-	8		nS
Turn-on Rise Time	tr	V _{DD} =10V,I _D =3.5A	-	17	-	nS
Turn-Off Delay Time	td(off)	V_{DD} = 10V,1D=3.5A V _{GS} =4.5V,R _{GEN} =6Ω	-	27	-	nS
Turn-Off Fall Time	t _f		-	8.8	-	nS
Total Gate Charge	Qg		-	11.3	-	nC
Gate-Source Charge	Qgs	V _{DS} =10V,I _D =7A,	-	1.89	-	nC
Gate-Drain Charge	Q _{gd}	V _{GS} =4.5V	-	3.56	-	nC
Diode Forward Voltage (Note 3)	Vsd	V _{GS} =0V,I _S =1.7A	-	0.75	1.2	V
Diode Forward Current (Note 2)	ls		-	-	7	A

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

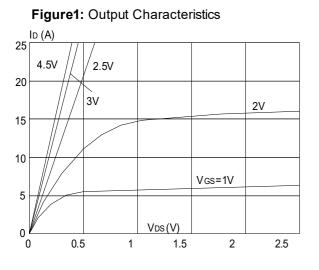
2. Surface Mounted on FR4 Board, $t \le 10$ sec.

3. Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.

4. Guaranteed by design, not subject to production



Typical Characteristics



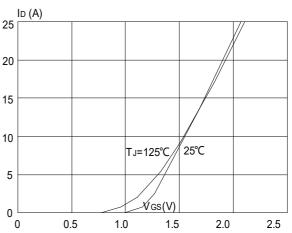
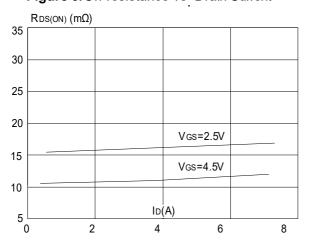
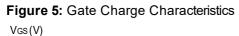


Figure 2: Typical Transfer Characteristics

Figure 3: On-resistance vs_ Drain Current





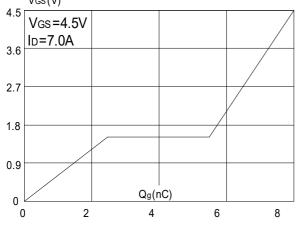


Figure 4: Body Diode Characteristics

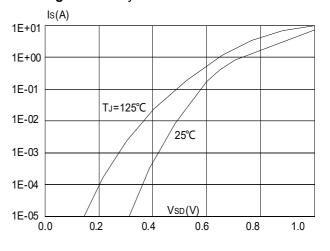
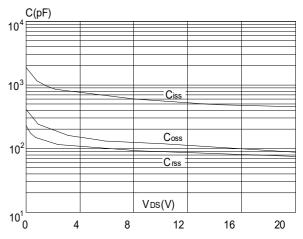


Figure 6: Capacitance Characteristics





DMG6968UTS Dual N-Channel Enhancement Mode MOSFET

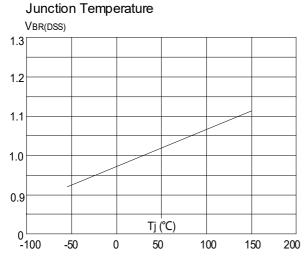
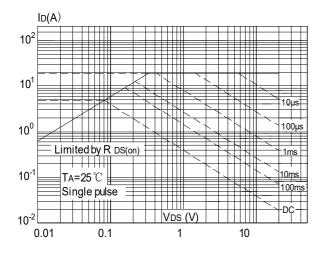
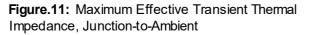
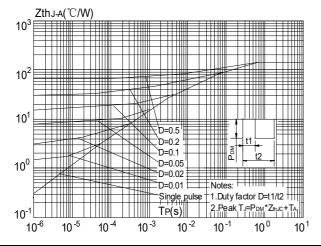


Figure 7: Normalized Breakdown Voltage vs.

Figure 9: Maximum Safe Operating Area







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Junction Temperature RDS(on) 2.0 1.5 1.0 0.5 -100 -50 0 50 100 150 200

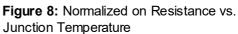
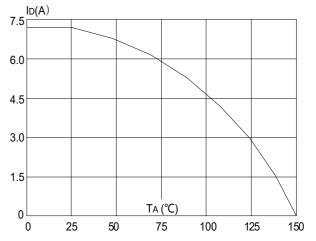
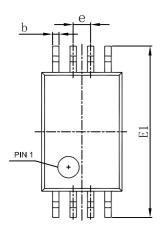


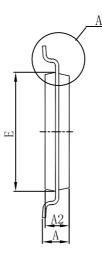
Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

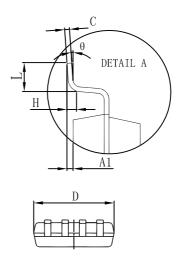




TSSOP-8 Package Outline Dimensions







Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
D	2.900	3.100	0.114	0.122	
Е	4.300	4.500	0.169	0.177	
b	0.190	0.300	0.007	0.012	
c	0.090	0.200	0.004	0.008	
E1	6.250	6.550	0.246	0.258	
А		1.200		0.047	
A2	0.800	1.000	0.031	0.039	
A1	0.050	0.150	0.002	0.006	
e	0.65 (BSC)		0. 026 (BSC)		
L	0.500	0.700	0.020	0.028	
Н	0.25(TYP)		0.01(TYP)		
θ	1°	7°	1°	7 °	



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